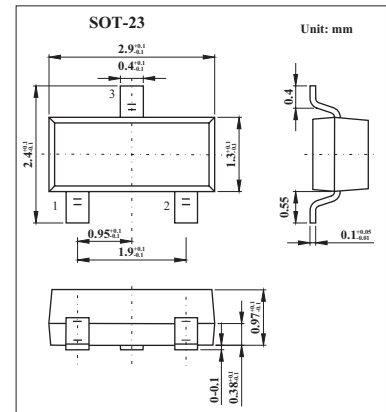


## Silicon Epitaxial Planar Diode

## HSM2693A

## ■ Features

- Low forward resistance. ( $r_f = 0.9 \text{ max}$ )
- Low capacitance. ( $C = 1.2 \text{ pFmax}$ )
- MPAK package is suitable for high density surface mounting and high speed assembly.

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

| Parameter             | Symbol    | Value       | Unit             |
|-----------------------|-----------|-------------|------------------|
| Reverse Voltage       | $V_R$     | 35          | V                |
| Power dissipation     | $P_d$     | 150         | mW               |
| Junction temperature  | $T_j$     | 125         | $^\circ\text{C}$ |
| Storage temperature   | $T_{stg}$ | -45 to +125 | $^\circ\text{C}$ |
| Operation temperature | $T_{opr}$ | -20 to +60  | $^\circ\text{C}$ |

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

| Parameter          | Symbol | Conditions                                | Min | Typ | Max | Unit     |
|--------------------|--------|---|-----|-----|-----|----------|
| Reverse voltage    | $V_R$  | $I_R = 10 \mu\text{A}$                    | 35  |     |     | V        |
| Reverse current    | $I_R$  | $V_R = 25 \text{ V}$                      |     |     | 50  | nA       |
| Forward voltage    | $V_F$  | $I_F = 10 \text{ mA}$                     |     |     | 1.0 | V        |
| Capacitance        | $C$    | $V_R = 6 \text{ V}, f = 1 \text{ MHz}$    |     |     | 1.2 | pF       |
| Forward resistance | $r_f$  | $I_F = 2 \text{ mA}, f = 100 \text{ MHz}$ |     |     | 0.9 | $\Omega$ |

## ■ Marking

| Marking | B4 |
|---------|----|
|         |    |